ERRATA

Equilibrium Shape of Si
[Phys. Rev. Lett. 70, 1643 (1993)]

D. J. Eaglesham, A. E. White, L. C. Feldman, N. Moriya, and D. C. Jacobson

The Si step energy of 28 ± 10 meV/atom determined from the curvature of small voids near (100) should more properly be compared with half of the double $A$-type step energy (i.e., $0.5 \times 50$ meV/atom [1]), as opposed to the single $B$-type step energy (23 meV/atom) used in this paper. The authors would like to thank Dr. H. J. W. Zandvliet for pointing this out.


Singular Behavior of Shear Flow Far from Equilibrium

A. Santos, V. Garzo, J. J. Brey, and J. W. Dufty

The matrix $\mathcal{L}$ given by Eq. (13) has two misprints: the element (5,9) should be $-\nu a$ rather than $\frac{K}{2} a$ and the element (7,6) should be $a$ rather than $-a$. The results reported in the paper have been obtained from the correct matrix $\mathcal{L}$.

The numerical value given in the paper for the diagonal element $c_3(a)$ is based on numerical calculations done by Ikenberry and Truesdell [J. Rat. Mech. Anal. 5, 1 (1956)]. A more accurate evaluation [Z. Alterman, K. Frankowski, and C. L. Pekeris, Astrophys. J. Suppl. Ser. 7, 291 (1962/3)] yields $c_3(a) = 4a(a) + 1.873\nu$, which leads to a modified value for the critical shear rate: $a_c \approx 6.845\nu$.

Surface-Tension-Gradient-Induced Pattern Formation in Monolayers

Mu Wang, G. Wildburg, J. H. van Esch, P. Bennema, R. J. M. Nolte, and H. Ringsdorf

We regret that there was a misspelling on the name of the last author. It should be H. Ringsdorf. The correct names of the authors should read as follows: Mu Wang, G. Wildburg, J. H. van Esch, P. Bennema, R. J. M. Nolte, and H. Ringsdorf.